AMENDMENT TO THE SPECIFICATION

Please amend paragraph [0030] as followed:

[0030] There are several methods by which a bulk heat dissipation substrate can be coupled to a semiconductor substrate. In one embodiment, the bulk heat dissipation substrate can be directly deposited on the semiconductor substrate. As illustrated in FIG. 4a, an untreated semiconductor wafer 410 is provided. A heat dissipation layer 420 is then deposited onto the semiconductor wafer 410. The deposition of the heat dissipation layer can be by chemical vapor deposition (CVD), atomic layer deposition, sputtering, or by any similar method. In an embodiment, where silicon carbide is deposited as the bulk heat dissipation substrate, CVD is one method of deposition. The bulk heat dissipation substrate can also be ~~deposited~~ formed by a direct bonding method where a wafer of the bulk heat dissipation substrate is bonded to a wafer of the semiconductor substrate. In this method, as illustrated in FIG. 4b, a transition layer 430 can be deposited onto the semiconductor wafer 410. The transition layer 430 can then be planarized to create a smooth surface to which a pre-formed bulk heat dissipation wafer 440 is bonded. There are two different direct bonding methods that may be employed. The first direct bonding method is the bond and split method and the second direct bonding method is the bond and grind back method.